Performance

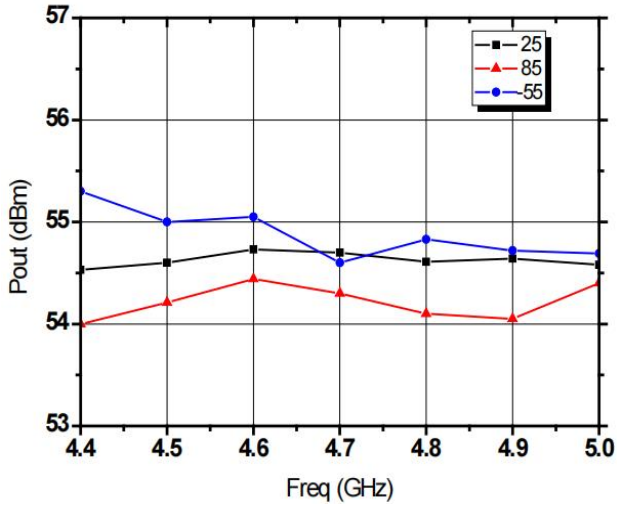
- Technology: 0.25um Power GaN HEMT
- Frequency: 4.4~5.0GHz
- Typical Pout : 54dBm
- Typical Gain: 10dB
- Typical PAE: 55%
- Bias: 32V/-2.8V
- Package: Metal Ceramic

Electrical Specifications (T_A=25℃,V_d=32V,Vg=-2.8V,Id≈12.8A,F: 4.4~5.0GHz,PL=1ms,D.C=15%)

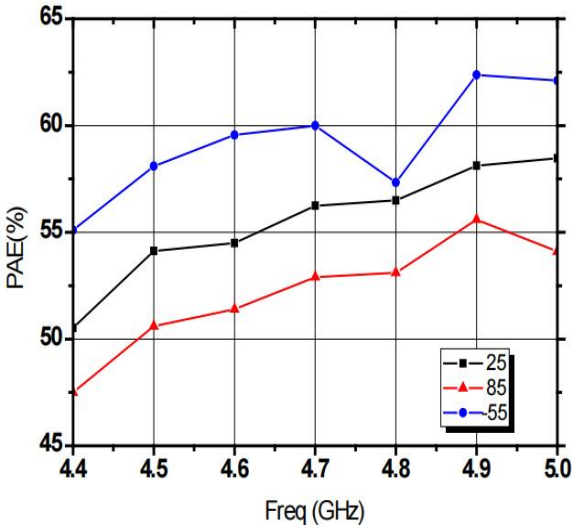
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	54	-	dBm
Gp	Power Gain	-	10	-	dB
ηadd	Power Added Efficiency	-	50	-	%
△Gp	Gain Flatness	-0.8	-	+0.8	dB

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

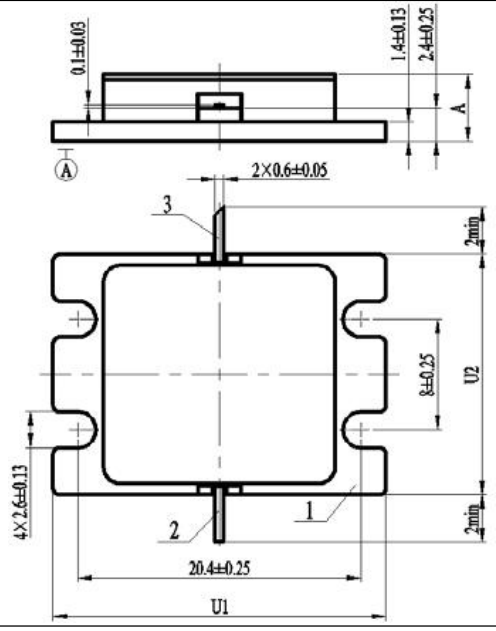


Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	500W	25℃
Tch	Channel Temperature	175℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

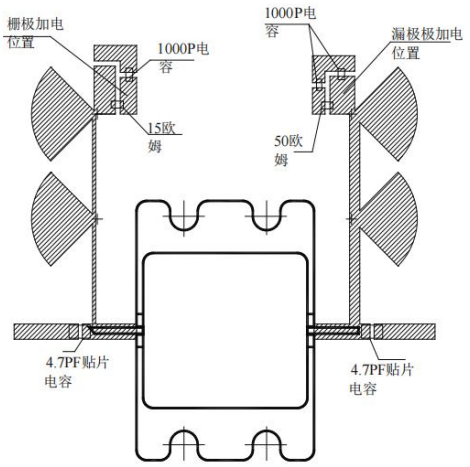
【1】Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Dimension Symbols



Symbol	Value（unit：mm）	
	Min.	Max.
U1	23.80	24.20
U2	17.20	17.60
A	-	5.2

Application Circuit



Note:

(1) This product is an internal matching tube, with input and output impedance values of 50 ohms;

(2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;

(3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 ℃;

(4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use.